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CLEAN VERSION OF ALL PENDING CLAIMS

1. (Twice amended) A method for making a transistor containing a gate dielectric structure, comprising:

providing a gate conductor;

providing a channel; and

providing, between the gate conductor and the channel, an oxide layer of the gate dielectric structure by an in-situ steam generation process.

2. (Cancelled)

3. (Amended) The method of claim 1, wherein the transistor is a thin film transistor.

4. (Cancelled)

5. (Amended) The method of claim 3, wherein the in-situ steam generation process is performed at a temperature ranging from about 600 to about 900 degrees Celsius.

6. The method of claim 1, wherein the in-situ steam generation process is performed at a pressure ranging from about 100 millitorr to about 760 torr.

7. The method of claim 1, wherein the in-situ steam generation process is performed for a time sufficient to deposit an oxide thickness of about 10 to about 200 angstroms.

8. (Amended) The method of claim 28, further including annealing the oxide layer in a nitric oxide atmosphere.

9. (Twice amended) A method for making a SONOS device, comprising:

providing a channel region;

providing a first oxide layer on the channel region by an in-situ steam generation process;

providing a nitride layer on the first oxide layer; and

providing a second oxide layer on the nitride layer.

10. (Cancelled)

11. (Cancelled)

12. The method of claim 9, wherein the in-situ steam generation process is performed at a temperature ranging from about 750 to about 1050 degrees Celsius.

13. The method of claim 9, wherein the in-situ steam generation process is performed at a pressure ranging from about 100 millitorr to about 760 torr.

14. The method of claim 9, wherein the in-situ steam generation process is performed for a time sufficient to deposit an oxide thickness of about 10 to about 200 angstroms.

15. The method of claim 9, further including annealing the oxide layer in a nitric oxide atmosphere.

16. (Cancelled)

17. (Cancelled)

18. (Cancelled)

19. (Cancelled)

20. (Amended) The method of claim 27, further including annealing the oxide layer in a nitric oxide atmosphere.

21. (Amended) A method for making a gate dielectric structure for a SONOS device, comprising:

providing silicon;

providing an oxide layer of a gate dielectric structure on the silicon by in-situ steam generation, the oxide layer having a thickness of about 10 to about 200 angstroms; and

annealing the oxide layer in a nitric oxide atmosphere.

22. (Amended) A method for making a gate dielectric structure for a thin film transistor or a SONOS device, comprising:

providing a gate conductor;

providing a channel region; and

providing, between the gate conductor and the channel region, an oxide layer of a gate dielectric structure by an in-situ steam generation process performed at a temperature ranging from about 600 to about 1050 degrees Celsius, a pressure ranging from about 100 millitorr to about 760 torr, and for a time sufficient to deposit an oxide thickness of about 10 to about 200 angstroms.

23. (Amended) A thin film transistor containing a gate dielectric structure made by a method comprising:

providing a gate conductor;

providing a channel region; and

providing, between the gate conductor and the channel region, an oxide layer of the gate dielectric structure on the channel region by an in-situ steam generation process.

24. (Twice amended) A SONOS semiconductor device made by a method comprising:

providing a channel region;

providing a first oxide layer on the channel region by an in-situ steam generation process;

providing a nitride layer on the first oxide layer; and

providing a second oxide layer on the nitride layer.

25. (Amended) An integrated circuit containing a thin film transistor with a gate dielectric structure made by a method comprising:

providing a gate conductor;

providing a channel; and

providing, between the gate conductor and the channel, an oxide layer of the gate dielectric structure by an in-situ steam generation process.

26. (Twice amended) An integrated circuit containing a SONOS semiconductor device made by a method comprising:

providing a silicon wafer or silicon layer;

providing a first oxide layer on the silicon wafer or silicon layer by an in-situ steam generation process;

providing a nitride layer on the first oxide layer; and

providing a second oxide layer on the nitride layer.

27. (New) The method of claim 1, wherein the transistor is a SONOS transistor.

28. (New) The method of claim 3, wherein the transistor is a SONOS transistor.

29. (New) The method of claim 3, wherein the transistor comprises a floating gate.

30. (New) The method of claim 21, wherein the silicon is a surface of a silicon wafer.

31. (New) The method of claim 21, wherein the silicon comprises polysilicon.

32. (New) The transistor of claim 23, wherein the transistor comprises a floating gate.

33. (New) The integrated circuit of claim 25, wherein the transistor comprises a floating gate.

34. (New) The transistor of claim 27, wherein the gate conductor comprises metal.